技术数据表

电性参数

=25 :Absolute Maximum Ratings (Temperature=25ÁC):

=25℃）：

Electro-Optical Charasteristics (Temperature=25ÁC):

Input	Forward Voltage	VF	IF=20mA	--	1.2	1.6	V
			IF=100mA*2	--	1.4	1.85	
			IF=1A *2	--	2.6	4.0	
	Perk Wavelength	∂P	IF=20mA	--	940	--	nm

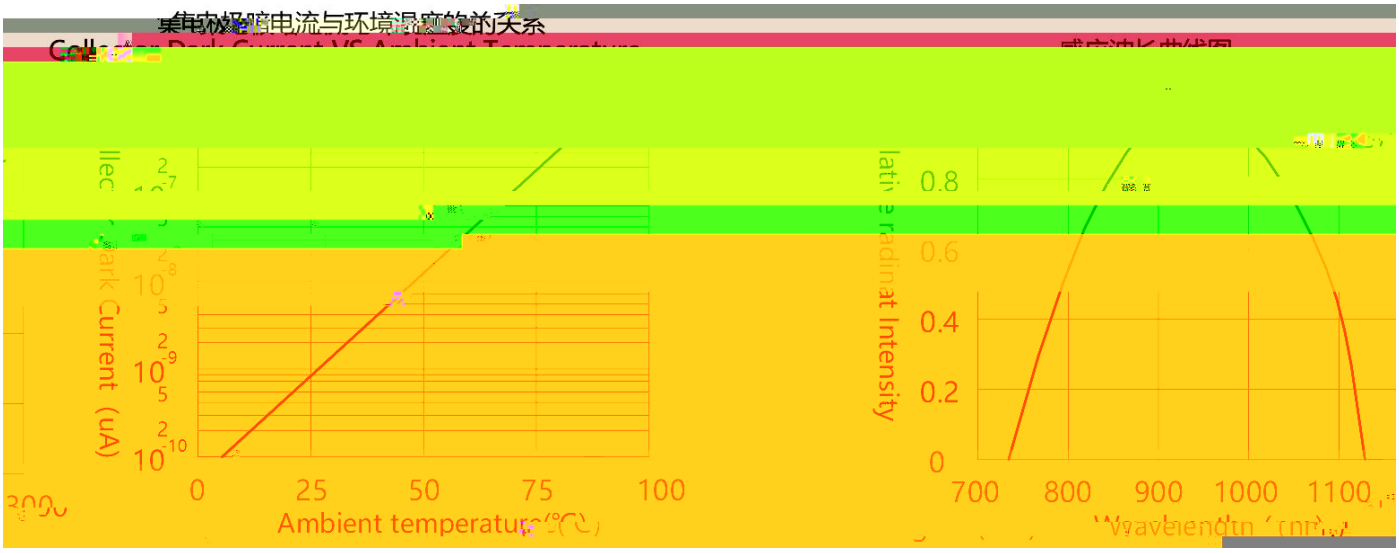
电压分档

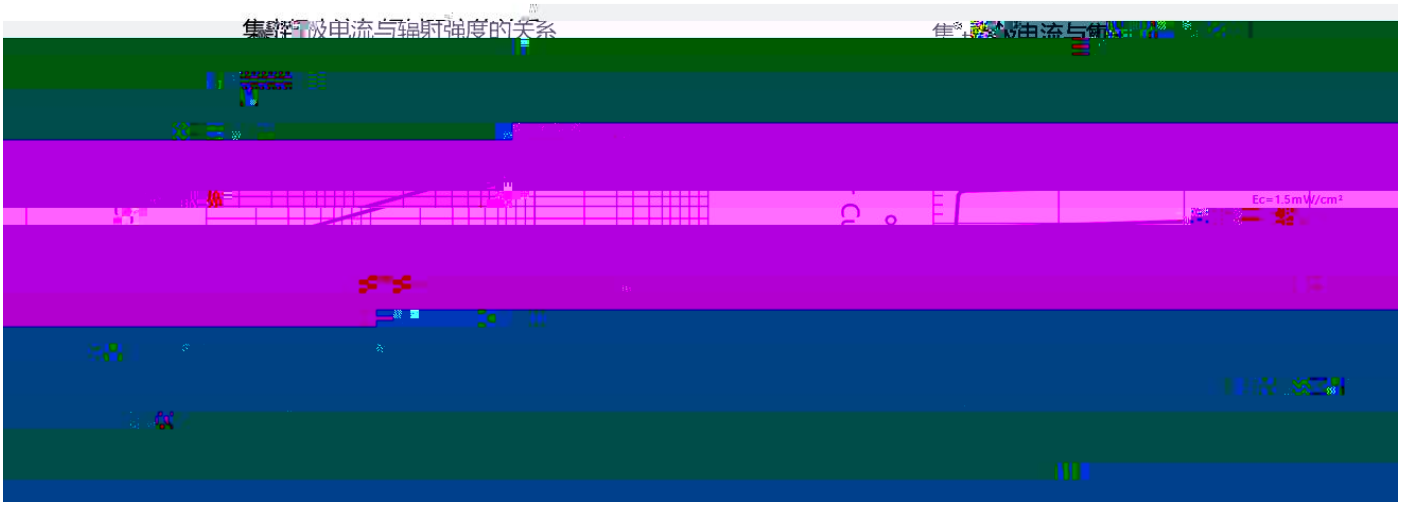
:

代码	最小值	最大值	单位	测试条件
R2-4	1.2	1.6	V	IF=20

典型特性曲线

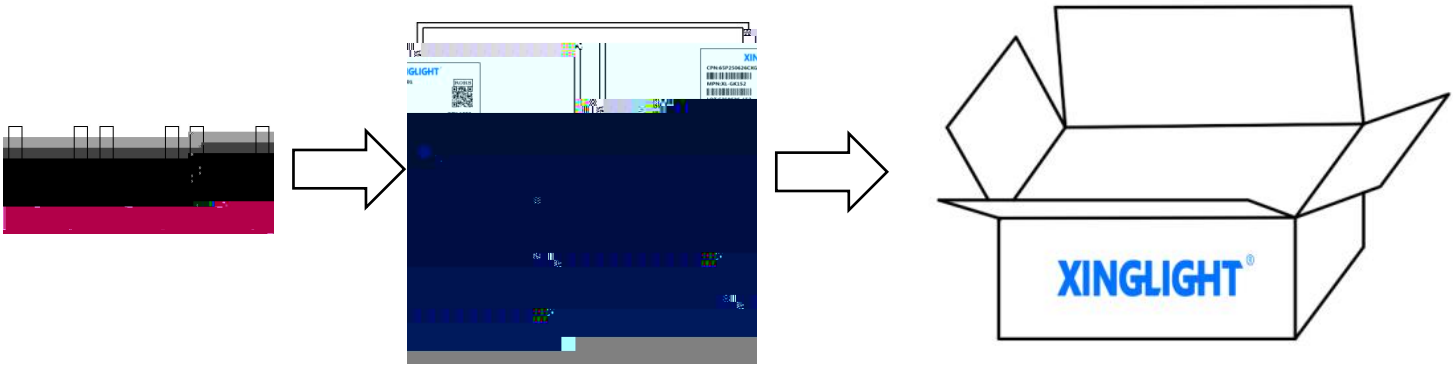
接收管特性曲线图


Dark Current (uA)
Ambient temperature(°C)
0
25
50
75
100
0.8
0.6
0.4
0.2
0
700
800
900
1000
1100



包装

Moisture Proof and Antti-Electrostic Foil Bag



Label Expantion

CPN：批号/档位　　LOT：日期

[illegible] a [illegible]lding [illegible]e is recom[illegible]nded

[illegible]

NPN

IR

IR PT

This product It is composed of infrared emission diode and NPN silicon photo transistor, which are packaged side by side in black On the converging optical axis in the thermoplastic shell. Photo transistor only receives radiation from IR. This is normal Condition. But when the object is in the middle, the photo transistor cannot receive radiation. For more component information, please Refķm " ˬ {